GUJARAT TECHNOLOGICAL UNIVERSITY BE - SEMESTER- III EXAMINATION – SUMMER 2015

Subject Code:131101 Date:02/06			2015	
T	Subject Name: Basic Electronics Time: 02.30pm-05.00pm Total Mar Instructions:			
	2	 Attempt all questions. Make suitable assumptions wherever necessary. Figures to the right indicate full marks. 		
Q.1	(a) (b)	Explain energy band diagram of insulator, semiconductor and conductor. Explain Hall Effect.	07 07	
Q.2	(a)	Explain (1) Tunnel Diode (2) Photodiode (3) I ED	07	
	(b)	(1) Tunnel Diode (2) Photodiode (3)LED.Explain V-I characteristic of p-n junction.	07	
		OR		
	(b)	Explain potential variation within graded semiconductor.	07	
Q.3	(a) (b)	Compare half wave rectifier with full wave rectifier. A 230V,50Hz.a.c voltage is applied to the primary of a 5:1 step down transformer which is used in a bridge rectifier having a load resistor of value 500Ω.Assuming the diode to be ideal, Determine the following: (1) d.c output voltage (2) d.c. power delivered to load (3)PIV of each diode (4) output frequency. OR	07 07	
Q.3	(a) (b)	Explain all types of clippers with examples. A half wave rectifier is utilized to supply 20V d.c to a resistive load of 400Ω . The diode used in half wave rectifier has a forward resistance of 40Ω . Determine the maximum value of the a.c voltage required at the input.	07 07	
Q.4	(a) (b)	Compare CB/CE/CC configurations Why bias stabilization is required in transistor? Explain any one method of transistor biasing.	07 07	
		OR		
Q.4	(a) (b)	Write down typical h-parameter values for CE/CB/CC configurations. Explain Miller's theorem.	07 07	
Q.5	(a) (b)	Compare JFET with MOSET Compare class A, class B, class C and class AB amplifiers	07 07	
		OR		
Q.5	(a)	Compare enhancement type MOSFET with depletion type MOSFET	07	

(b) For N-channel JFET, $I_{DSS}=20$ mA, $V_p=-8V$, and $g_{mo}=5000$ µs. Find the values of the 07 drain current and trans conductance at $V_{gs}=-4V$
